

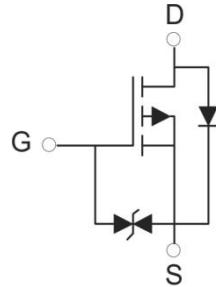
### **Feature**

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected

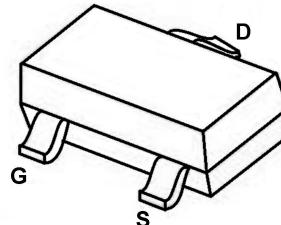
### **Application**

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

### **Circuit diagram**



### **Package :TP**



**SOT-523**

### **Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	-0.8	A
Pulsed Drain Current	I <sub>DM</sub>	-1.2	A
Power Dissipation	P <sub>D</sub>	0.15	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

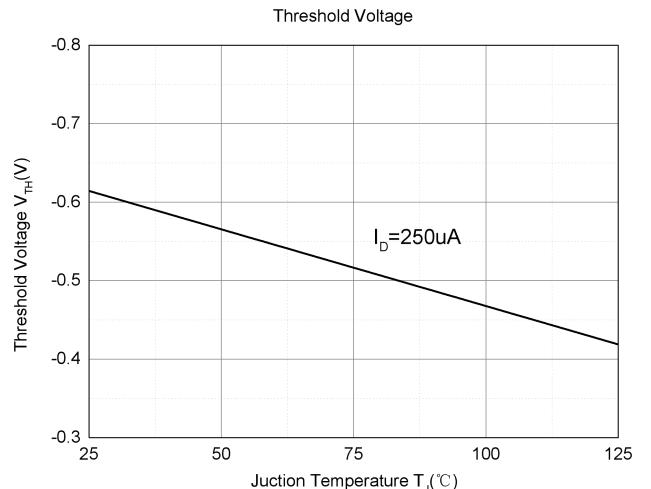
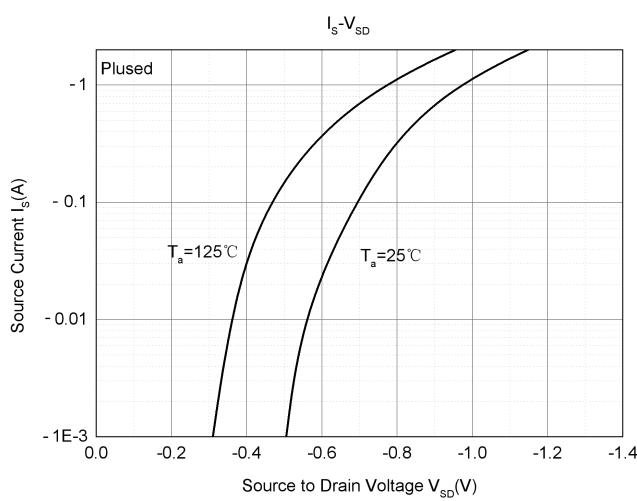
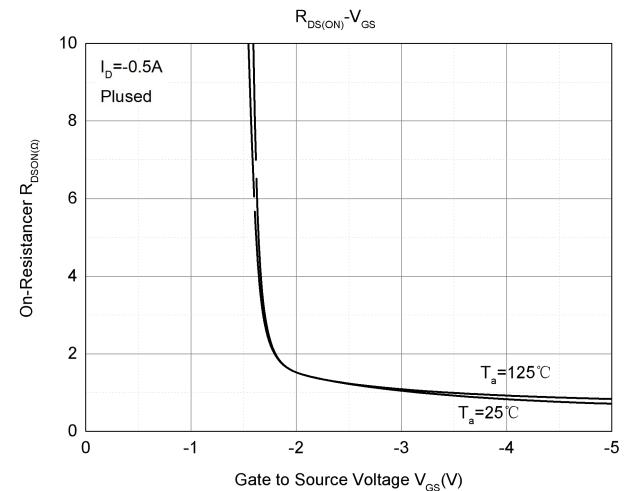
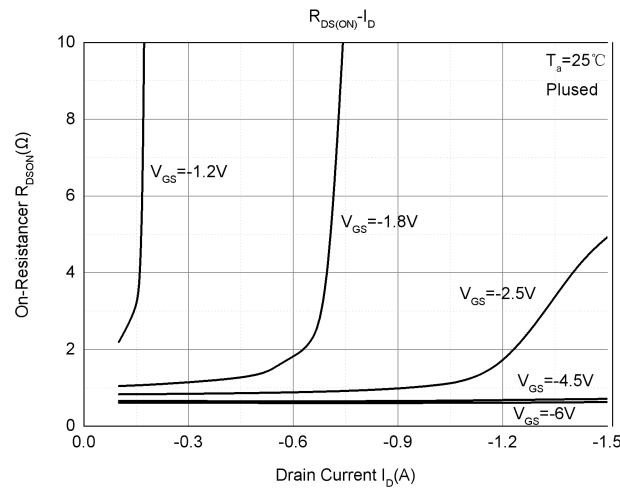
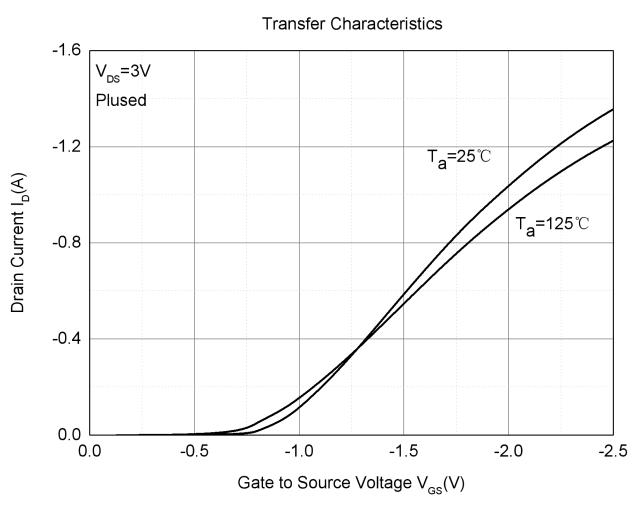
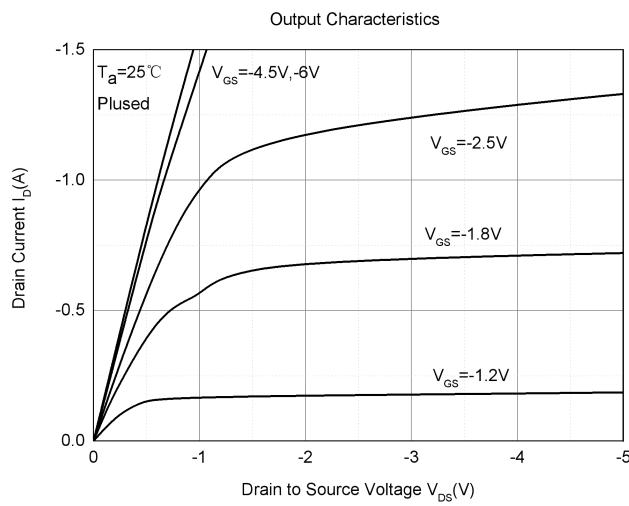
**Electrical characteristics ( $T_A=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = -16\text{V}, V_{\text{GS}} = 0\text{V}$			-1	$\mu\text{A}$
Gate-body leakage current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 10\text{V}, V_{\text{DS}} = 0\text{V}$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.35	-0.65	-1	V
Drain-source on-resistance <sup>1)</sup>	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -0.8\text{A}$		290	375	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_D = -0.6\text{A}$		380	495	
		$V_{\text{GS}} = -1.8\text{V}, I_D = -0.3\text{A}$		555		
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		113		$\text{pF}$
Output Capacitance	$C_{\text{oss}}$			15		
Reverse Transfer Capacitance	$C_{\text{rss}}$			9		
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}} = -10\text{V}, I_D = -200\text{mA}, V_{\text{GS}} = -4.5\text{V}, R_G = 10\Omega$		9		$\text{ns}$
Turn-on rise time	$t_r$			5.7		
Turn-off delay time	$t_{\text{d}(\text{off})}$			32.6		
Turn-off fall time	$t_f$			20.3		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$V_{\text{SD}}$	$V_{\text{GS}} = 0\text{V}, I_s = -0.5\text{ A}$			-1.2	V

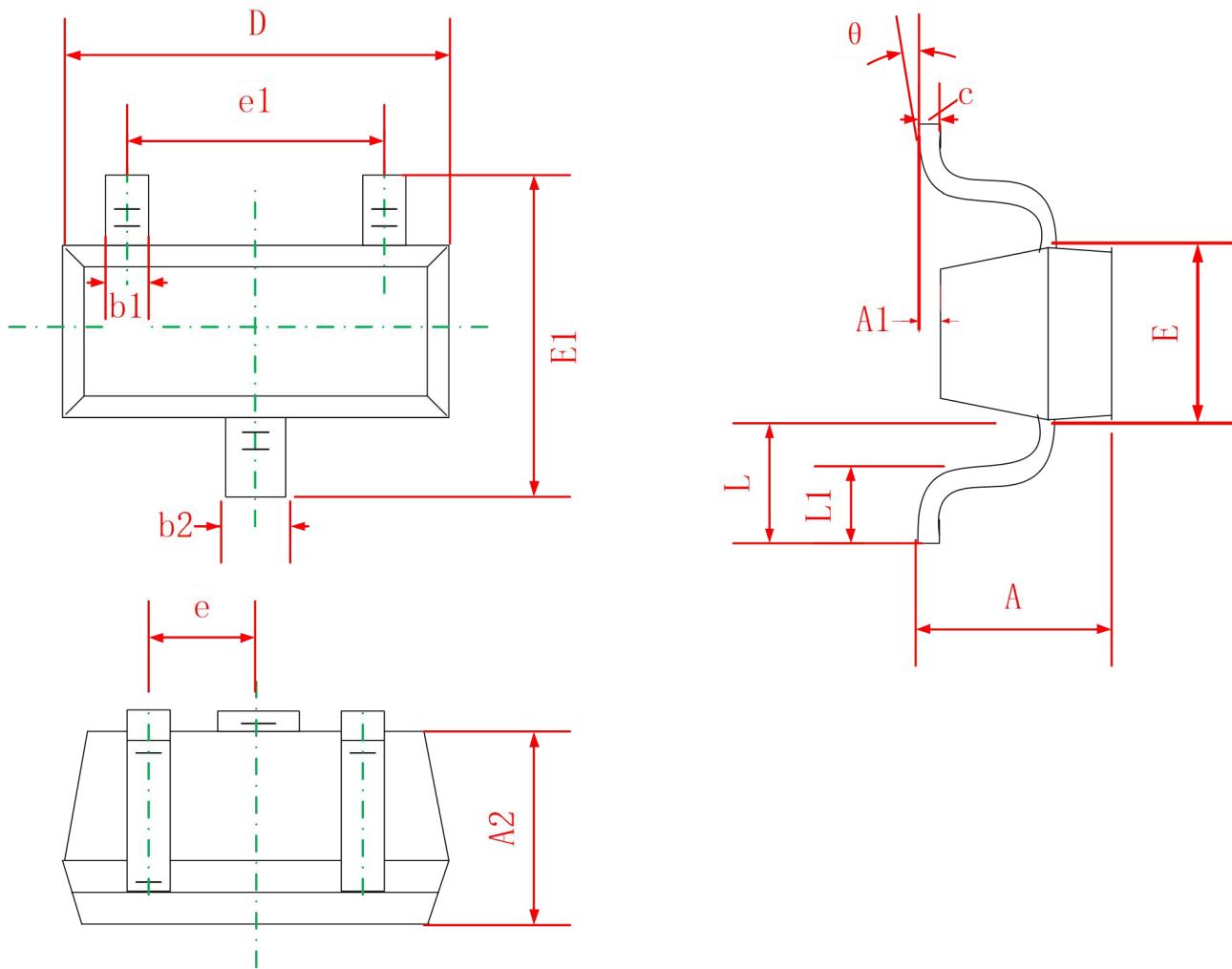
Notes:

- 1) Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics



### SOT 523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°